OPB816Z



Features:

- 0.20" (5.1 mm) wide gap, 0.61" (15.5 mm) deep slot
- Wire length 24" (609 mm) minimum, 26 AWG
- Dust protection
- Two mounting tabs



Description:

The OPB816Z slotted switch consists of an infrared emitting diode and an NPN silicon phototransistor mounted in an opaque housing with clear windows for dust protection. Switching of the phototransistor occurs whenever an opaque object passes through the slot.

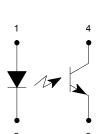
The OPB816Z has an 0.61" (15.5 mm) deep slot allowing for a longer reach of the optical center line from the mounting plane. The phototransistor internal apertures are 0.010" x 0.06" (0.25 mm x 1.52 mm) on the sensor side ("S") and 0.05" x 0.06" (1.27 mm x 1.52 mm) on the emitter side ("E").

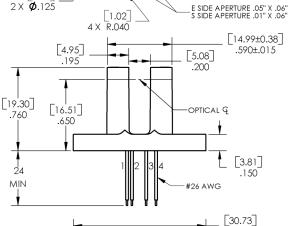
.100

Applications:

- Non-contact object sensing
- Assembly line automation
- Machine automation
- Equipment security
- Machine safety

| Ordering Information | | | | |
|-------------------------|----------------|--|--|--|
| Part Number Description | | | | |
| OPB816Z | Slotted switch | | | |





[12.19]

.480

[3.18] 2 X **Ø**.125

| Color/Pin # | Description | | | |
|-------------|-------------|--|--|--|
| Red | Anode | | | |
| Black | Cathode | | | |
| Green | Emitter | | | |
| White | Collector | | | |



| [6.35] .250 [24.38] .960 | [30.73] 1.21 [1.35±0.51] .053±.02 | [MILLIMETERS] |
|--------------------------------|--|----------------|
| [8.76±0.51] .345±.02 | [7.87±0.51] .310±.02 | INCHES |

[3.18]

General Note

OPB816Z



Electrical Specifications

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

| Storage & Operating Temperature Range | -40°C to +85° C |
|--|-----------------|
| Lead Soldering Temperature [1/16 inch (1.6mm) from the case for 5 sec. with soldering iron] ⁽¹⁾ | 260° C |

Input Diode (see OP140 for additional information)

| Forward DC Current | 50 mA |
|--|--------|
| Peak Forward Current (1 μs pulse width, 300 pps) | 3 A |
| Reverse DC Voltage | 2 V |
| Power Dissipation ⁽²⁾ | 100 mW |

Output Phototransistor (See OP552 for additional information)

| Collector-Emitter Voltage | 30 V |
|----------------------------------|--------|
| Emitter-Collector Voltage | 5 V |
| Collector DC Current | 30 mA |
| Power Dissipation ⁽²⁾ | 100 mW |

Electrical Characteristics (T_A = 25°C unless otherwise noted)

| SYMBOL | PARAMETER | MIN | TYP | MAX | UNITS | TEST CONDITIONS | |
|------------------------|--|--------|-----|------|-------|---|--|
| Input Diode | Input Diode (see OP140 for additional information) | | | | | | |
| V_{F} | Forward Voltage | - | 1 | 1.8 | ٧ | I _F = 20 mA | |
| I _R | Reverse Current | - | - | 100 | μΑ | V _R = 2 V | |
| Output Pho | totransistor (see OP552 for additional informa | ation) | | | | | |
| V _{(BR)(CEO)} | Collector-Emitter Breakdown Voltage | 30 | 1 | -1 | V | $I_C = 1 \text{ mA}, I_F = 0, E_E = 0$ | |
| V _{(BR)(ECO)} | Emitter-Collector Breakdown Voltage | 5 | 1 | 1 | ٧ | $I_E = 100 \ \mu A, I_F = 0, E_E = 0$ | |
| I _{CEO} | Collector-Emitter Leakage Current | - | 1 | 100 | nA | $V_{CE} = 10 \text{ V}, I_F = 0, E_E = 0$ | |
| Coupled | | | | | | | |
| I _{C(ON)} | On-State Collector Current | 1.0 | - | 10.0 | mA | V _{CE} = 5 V, I _F = 20 mA | |

0.4

V_{CE(SAT)} Notes:

- (1) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- (2) Derate linearly 1.67 mW/°C above 25° C.

Collector-Emitter

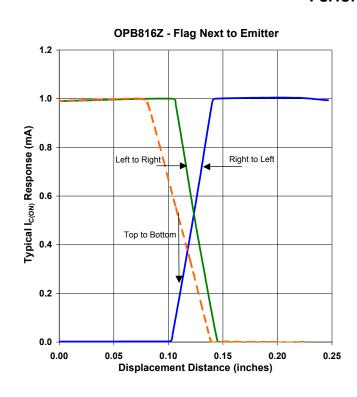
- (3) All parameters are tested using pulse techniques.
- (4) Methanol or isopropanol are recommended as cleaning agents. Plastic housing is soluble in chlorinated hydrocarbons and ketones.
- (5) Clear dust protection over emitter and sensor apertures.

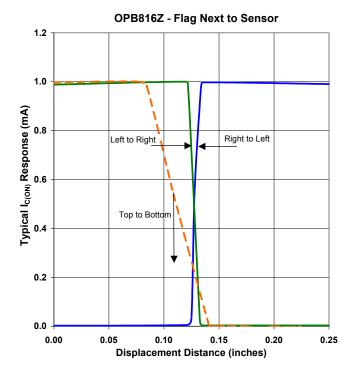
 $I_C = 100 \mu A$, $I_F = 20 mA$

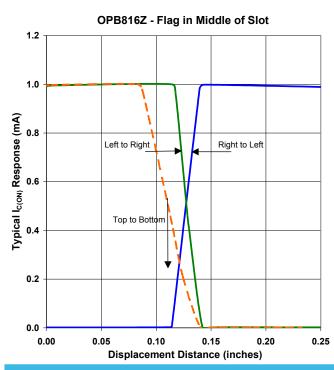
OPB816Z

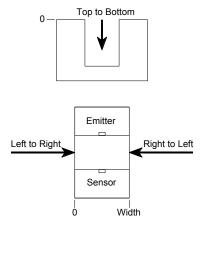


Performance









General Note

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.





| A. I Revised and put into new format. Required changes on all pages. A.1 Changed internal apertures in 2nd paragraph from 0.10" to 0.010" (R.Parks), Did not change revision number or issue date. 99/13/13 | Issue | Change Description | Approval | Date |
|---|-------|---|-------------|----------|
| Changed internal apertures in 2nd paragraph from 0.10" to | A | Initial Release | | |
| A.1 Changed internal apertures in 2nd paragraph from 0.10" to 0.010" (R. Parks). Did not change revision number or issue date. 09/13/13 | A.1 | Revised and put into new format. Required changes on all pages. | Steve Coble | 12/07/05 |
| | A.1 | Changed internal apertures in 2nd paragraph from 0.10" to 0.010" (R.Parks). Did not change revision number or issue date. | | 09/13/13 |
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